

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1. – 15. (Canceled)

16. (New) A semiconductor device comprising:

a semiconductor substrate;

a field area including a semiconductor insulating layer on the semiconductor substrate and a plurality of active areas adjacent to the field area;

a p-type first field effect type transistor and a p-type second field effect transistor disposed in a first active area;

an n-type first field effect transistor and an n-type second field effect transistor disposed in a second active area;

wherein the p-type first field effect type transistor, p-type second field effect transistor, n-type first field effect transistor and n-type second field effect transistor structures constitute a sense amplifier circuit;

a third active area disposed between said first active area and said second active area;

a fourth active area disposed in said first active area across the third active area; and

a fifth active area disposed in the second active area across the third active area;

wherein the difference between the distance between the first active area and the third active area and the distance between the first active area and the fourth active area is set to be smaller than the difference between the distance between the first active area and the third active area and the distance between the second active area and the third active area.

17. (New) A semiconductor device comprising:

a semiconductor substrate;

a field area including a semiconductor insulating layer on the semiconductor substrate and a plurality of active areas adjacent to the field area;

a p-type first field effect transistor and a p-type second field effect transistor disposed in a first active area;

an n-type first field effect transistor and an n-type second field effect transistor disposed in a second active area;

wherein the p-type first field effect transistor, the p-type second field effect transistor, the n-type first field effect transistor and the n-type second field effect transistor constitute a sense amplifier;

a third active area formed between the first active area and the second active area;

a fourth active area disposed in the first active area across the third active area; and

a fifth active area disposed in the second active area across the third active area;

wherein the difference of the distance between the first active area and the third active area and the distance between the second active area and the fifth active area is set to be smaller than the difference between the distance of the first active area and the third active area and the distance between the second active area and the third active area.

18. (New) A semiconductor device according to claim 16, wherein the third active area and the first active area include substantially the same area in a longitudinal direction as in the second active area.

19. (New) A semiconductor device according to claim 16, wherein the first active area and the second active area include substantially the same area in the longitudinal direction.

20. (New) A semiconductor device according to claim 16, wherein a disposing direction of the p-type second field effect transistor relative to the p-type first field effect transistor is formed in a direction to traverse the longitudinal direction of the first active area.

21. (New) A semiconductor device according to claim 16, wherein a disposing direction of the n-type second field effect transistor relative to the n-type first field effect transistor is formed in a direction to traverse the longitudinal direction of the second active area.